# 2SC4691G

### Silicon NPN epitaxial planar type

For high-speed switching

#### Features

- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing
- Package
- Code
- SSMini3-F3
- Marking Symbol: 2Y
- Pin Name
  - 1. Base
  - 2. Emitter
  - 3. Collector

Absolute Maximum	Ratings	$T_a = 25^{\circ}C$
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Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	40	v	
Collector-emitter voltage (E-B short)	V <sub>CES</sub>	40	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	v	
Collector current	I <sub>C</sub>	100	mA	
Peak collector current	I <sub>CP</sub>	300	mA	
Collector power dissipation	P <sub>C</sub>	125	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°Ç	

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 40 \text{ V}, I_E = 0$	X0~	S	0.1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 4 V, I_C = 0$	s S	, v	0.1	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 10 \text{ mA}$	60		200	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}$		0.17	0.25	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1 \text{ mA}$			1.0	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$		450		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2	6	pF
Turn-on time	t <sub>on</sub>	Refer to the measurement circuit		17		ns
Turn-off time	t <sub>off</sub>	and the		17		ns
Storage time	t <sub>stg</sub>			10		ns

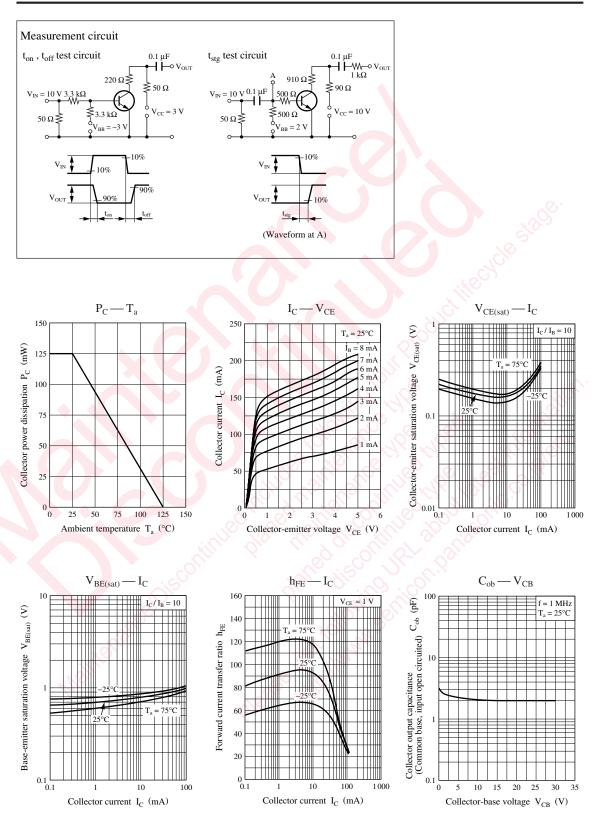
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

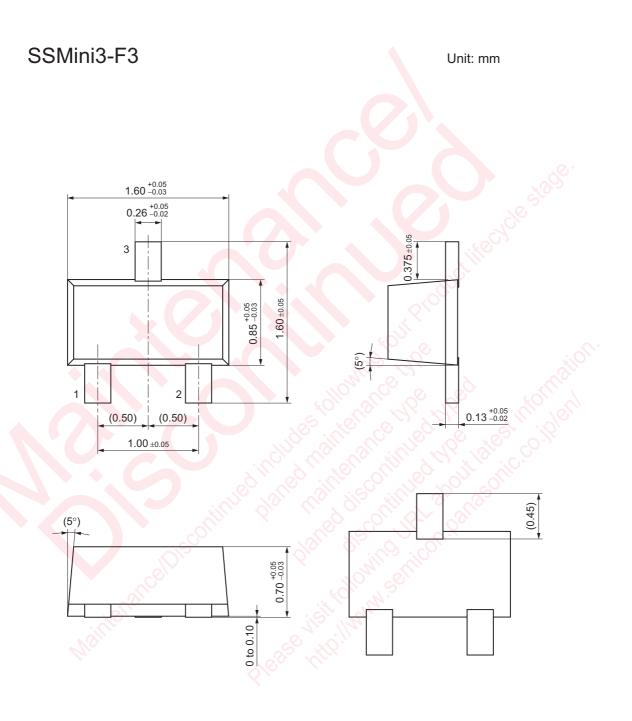
2. \*: Rank classification

Rank	Q	R	No-rank	
h <sub>FE</sub>	60 to 120	90 to 200	60 to 200	

Product of no-rank is not classified and have no indication for rank.

## Panasonic





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